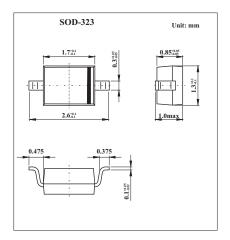
SMD Type Diodes

Surface Mount Schottky Barrier Diode KB160M-20

■ Features

- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop



■ Absolute Maximum Ratings Ta = 25°C

Parameter		Symbol	Rating	Unit
Peak repetitive Peak reverse voltage		Vrrm		
Working Peak Reverse Voltage		VRWM	20	V
DC Blocking Voltage		Vr		
RMS Reverse Voltage		VR(RMS)	14	V
Average Rectified Output Current (Note 1)	@TL = 90°C	lo	1	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)		Iғsм	25	А
Forward Voltage	@IF = 1.0A	VF	0.45	V
	@IF = 3.0A		0.75	
Peak Reverse Current	@Ta = 25°C	lR	1	mA
At Rated DC Blocking Voltage	@Ta = 100°C		10	
Thermal Resistance Junction to Ambient		R ⊕ JA	500	°C//W
Operating and Storage Temperature Range		Тj, Tsтg	-65 to 150	°C

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

■ Marking

Marking	SJ

SMD Type Diodes

KB160M-20

Typical Characteristics

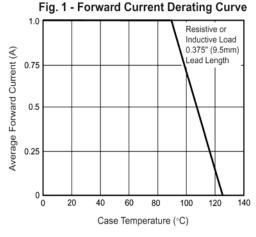


Fig. 2 - Maximum Non-Repetitive Peak **Forward Surge Current**

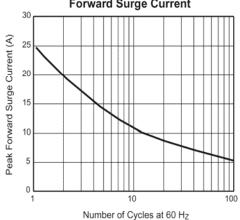


Fig. 3 - Typical Instantaneous Forward Characteristics

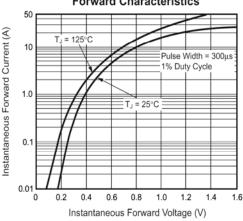


Fig. 4 - Typical Reverse Characteristics

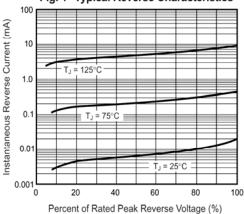


Fig. 5 - Typical Junction Capacitance

